				April 1999			
	359AN hannel L	ogic Level P	owerTrench <sup>™</sup> I	MOSFET			
Genera	al Descriptio	on		Features			
This N-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance. These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.				<ul> <li>2.7 A, 30 V. R<sub>DS(ON)</sub> = 0.046 Ω @ V<sub>GS</sub> = 10 V R<sub>DS(ON)</sub> = 0.060 Ω @ V<sub>GS</sub> = 4.5 V.</li> <li>Very fast switching.</li> <li>Low gate charge (5nC typical).</li> <li>High power version of industry standard SOT-23 package. Identical pin out to SOT-23 with 30% higher power handling capability.</li> </ul>			
				SO-8	SOT-223	SOIC-16	
SC	DT-23	SuperSOT <sup>™</sup> -6	SuperSOT <sup>™</sup> -8				
SC							
Absol	Supe	D 359A 359A G					
Absol	Supe ute Maxim Parameter	$\frac{D}{359A}$ rsot <sup>T</sup> -3 G um Ratings T <sub>A</sub> =	s		G S	Units	
Absol Symbol	Supe	D 359A G rSOT™-3 G um Ratings T <sub>A</sub> =	s		G S Ratings	Units V	
Absol Symbol / <sub>css</sub>	Supe ute Maxim Parameter Drain-Sourc Gate-Sourc	$\frac{D}{359A}$ $\frac{359A}{G}$ $G$ $T_{-3}$ $G$ $T_{A} = \frac{1}{2}$ $E \text{ Voltage}$ $E \text{ Voltage}$	S		D         G       S         G       S         Ratings       30         ±20       ±20	Units UV V	
Absol Symbol / <sub>css</sub>	Supe ute Maxim Parameter Drain-Sourc Gate-Sourc	D 359A G rSOT™-3 G um Ratings T <sub>A</sub> =	S = 25°C unless other wise		G S Ratings	Units V	
Absol Symbol /oss /oss	Supe Lute Maxim Parameter Drain-Sourc Gate-Sourc Maximum E	$\frac{D}{359}A$ $r_{SOT} = 3$ $G$ $T_{A} = 0$	S = 25°C unless other wise		D         G       S         G       S         Ratings       30         ±20       2.7	Units UV V	
Absol Symbol /oss /oss	Supe Lute Maxim Parameter Drain-Sourc Gate-Sourc Maximum E	$D$ $359A$ $G$ $FSOT \xrightarrow{M} 3$ $G$ $T_A =$ $Drain Current - Continu - Pulse$	S S = 25°C unless other wise		D         G       S         G       S         Ratings       30         ±20       2.7         15       15	Units V V A	
Absol Symbol /pss /gss p 2 p	Supe	$D$ $359A$ $G$ $FSOT \xrightarrow{M} 3$ $G$ $T_A =$ $Drain Current - Continu - Pulse$	S S S S S S S S S S S S S S S S S S S		D           G         S           G         S           Ratings         30           ±20         2.7           15         0.5	Units V V A	
Absol Symbol /oss /oss D	Supe	D $G$	S S S S S S S S S S S S S S S S S S S		D           G         S           G         S           Ratings         S           30         ±20           2.7         15           0.5         0.46	Units UV V A W W	
Absol Symbol /oss /oss D D D	Supe	D $G$	S S = 25°C unless other wise ious (Note 1a) ed (Note 1a) (Note 1b) ure Range		D           G         S           G         S           Ratings         S           30         ±20           2.7         15           0.5         0.46	Units UV V A W W	

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Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CHAR	ACTERISTICS	·					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$		30			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	$I_{D}$ = 250 µA, Referenced to	0 25 ℃		23		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{\rm DS} = 24  \text{V},   \text{V}_{\rm GS} = 0  \text{V}$				1	μA
			T <sub>J</sub> = 55°C			10	μA
	Gate - Body Leakage, Forward	$V_{GS} = 20 V, V_{DS} = 0 V$	•			100	nA
	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
	CTERISTICS (Note)	·			•		
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		1	1.6	3	V
$\Delta V_{GS(th)} / \Delta T_J$	Gate Threshold Voltage Temp. Coefficient	$I_{\rm D}$ = 250 µA, Referenced to	$I_D = 250 \ \mu\text{A}$ , Referenced to $25 \ ^{\circ}\text{C}$		-4		mV/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 2.7 \text{ A}$			0.037	0.046	Ω
			T <sub>J</sub> =125°C		0.055	0.075	
		$V_{GS} = 4.5 \text{ V}, I_{D} = 2.4 \text{ A}$			0.049	0.06	
I <sub>D(ON)</sub>	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$		15			Α
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5 V, I_{D} = 2.7 A$			9.5		S
DYNAMIC C	HARACTERISTICS						
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz			480		pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz			120		pF
C <sub>rss</sub>	Reverse Transfer Capacitance				45		pF
SWITCHING	CHARACTERISTICS (Note)						
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{DD} = 5 V, I_D = 1 A,$ $V_{GS} = 4.5 V, R_{GEN} = 6 \Omega$			6	12	ns
ţ	Turn - On Rise Time				13	24	ns
t <sub>D(off)</sub>	Turn - Off Delay Time				15	27	ns
t,	Turn - Off Fall Time				4	10	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = 10 \text{ V}, \ \text{I}_{D} = 2.7 \text{ A},$			5	7	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = 5 V$			1.4		nC
Q <sub>gd</sub>	Gate-Drain Charge				1.6		nC
DRAIN-SOL	IRCE DIODE CHARACTERISTICS AND M	AXIMUM RATINGS					
l <sub>s</sub>	Maximum Continuous Drain-Source Diode F	orward Current				0.42	А
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	rce Diode Forward Voltage $V_{GS} = 0 \text{ V}, I_{S} = 0.42 \text{ A}_{(Note)}$			0.65	1.2	V

Note:

1. R<sub>eux</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>euc</sub> is guaranteed by design while R<sub>eck</sub> is determined by the user's board design.

Typical  $\rm R_{_{BJA}}$  using the board layouts shown below on FR-4 PCB in a still air environment :



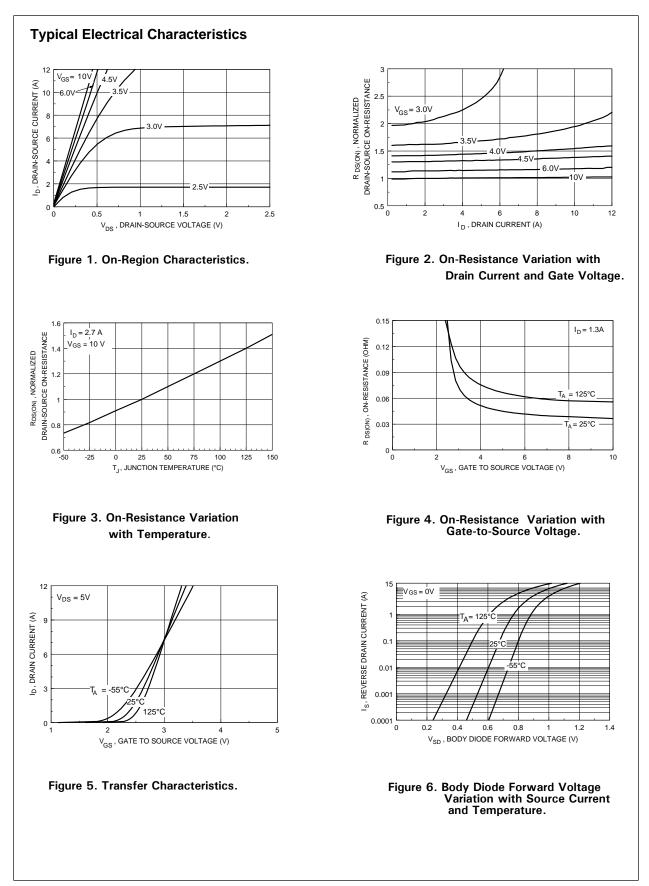
a. 250°C/W when mounted on a 0.02 in<sup>2</sup> pad of 2oz Cu.

Î 7

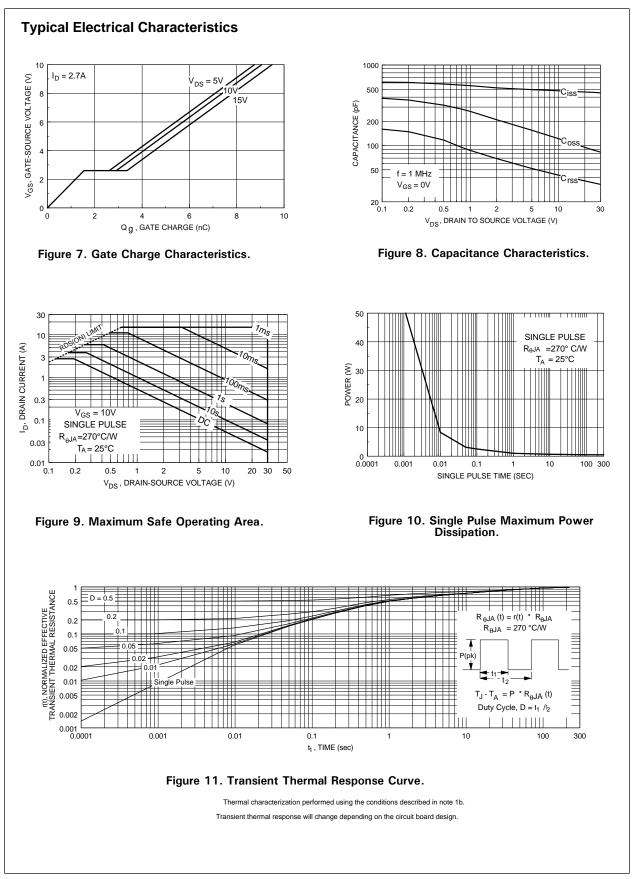
b. 270°C/W when mounted on a minimum pad.

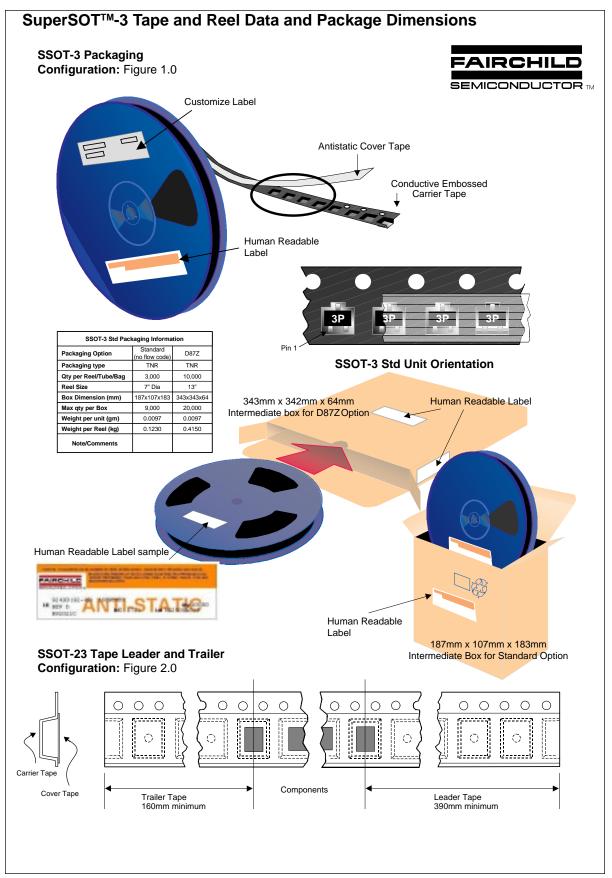
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2.0%.

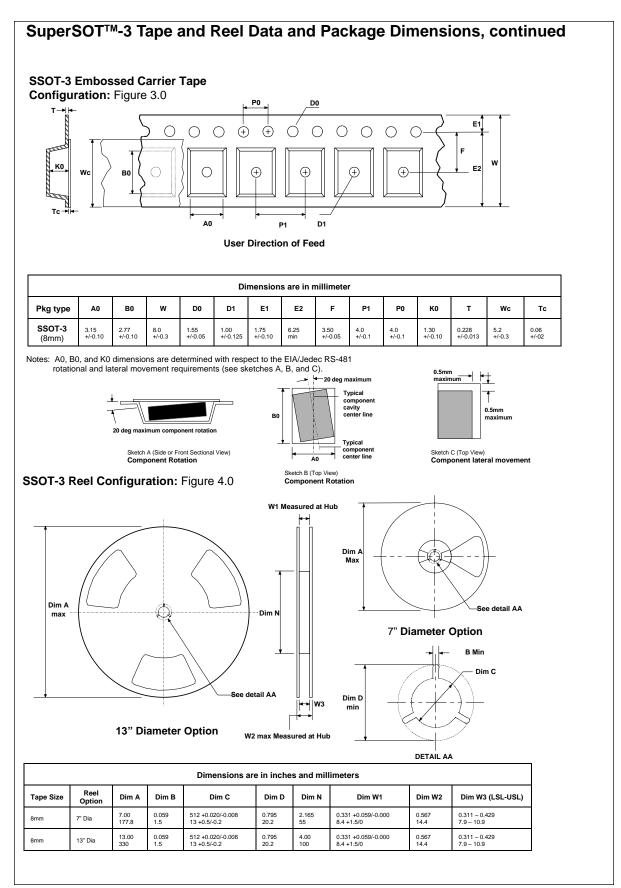


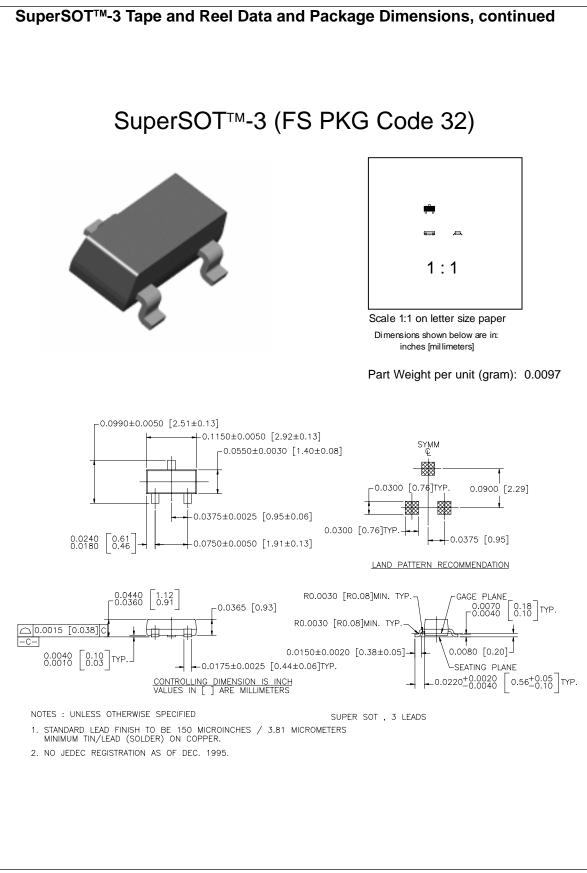
FDN359AN Rev.C





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